

16A, 500V N-CHANNEL POWER MOSFET

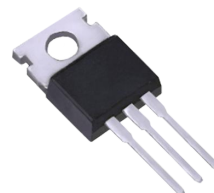
■ DESCRIPTION

The UTC **16N50** is a N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology allows a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

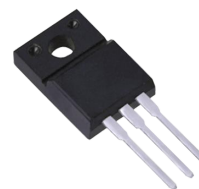
The UTC **16N50** is generally applied in high efficiency switch mode power supplies, active power factor correction and electronic lamp ballasts based on half bridge topology.

■ FEATURES

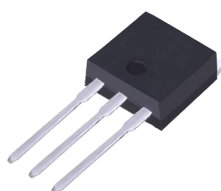
- * $R_{DS(ON)} \leq 0.38\Omega$ @ $V_{GS}=10V$, $I_D=8.0A$
- * High Switching Speed
- * 100% Avalanche Tested



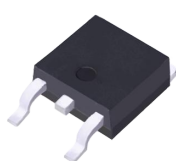
T0-220



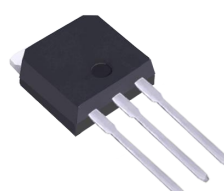
T0-220F



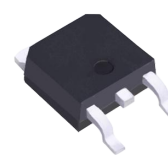
T0-262



T0-263



T0-251



T0-252

■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	500	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	16	A
	Pulsed (Note 2)	I_{DM}	64	A
Avalanche Current (Note 2)		I_{AR}	12.9	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	832	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	3.8	V/ns
Power Dissipation	TO-220	P_D	220	W
	TO-220F1/TO-220F2		38	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. $L=10\text{mH}$, $I_{AS}=12.9\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD}\leq 16\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220	θ_{JC}	0.57	$^\circ\text{C}/\text{W}$
	TO-220F1/TO-220F2		3.29	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	500			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=500\text{V}$, $V_{GS}=0\text{V}$			10	μA
Gate- Source Leakage Current	Forward	I_{GSS}			+100	nA
	Reverse				-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=8\text{A}$			0.38	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$, $f=1.0\text{MHz}$		2330		pF
Output Capacitance	C_{OSS}			260		pF
Reverse Transfer Capacitance	C_{RSS}			29		pF
SWITCHING PARAMETERS						
Total Gate Charge (Note 1)	Q_G	$V_{DS}=50\text{V}$, $V_{GS}=10\text{V}$, $I_D=1.3\text{A}$, $I_D=100\mu\text{A}$ (Note 1, 2)		170		nC
Gate to Source Charge	Q_{GS}			16		nC
Gate to Drain Charge	Q_{GD}			35.5		nC
Turn-ON Delay Time (Note 1)	$t_{D(ON)}$	$V_{DS}=30\text{V}$, $V_{GS}=10\text{V}$, $I_D=0.5\text{A}$, $R_G=25\Omega$ (Note 1, 2)		114		ns
Rise Time	t_R			121		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			590		ns
Fall-Time	t_F			185		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				16	A
Maximum Body-Diode Pulsed Current	I_{SM}				64	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	$I_S=16\text{A}$, $V_{GS}=0\text{V}$			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t_{rr}	$I_S=16\text{A}$, $V_{GS}=0\text{V}$, $dI_F/dt=100\text{A}/\mu\text{s}$		375		nS
Body Diode Reverse Recovery Charge	Q_{rr}			5.25		μC

Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating ambient temperature.

TYPICAL CHARACTERISTICS

